



BC857CQ

#### 45V PNP SMALL SIGNAL TRANSISTOR IN SOT23

#### **Description**

This Bipolar Junction Transistors (BJT) are designed to meet the stringent requirements of Automotive Applications.

#### **Features**

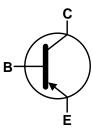
- · Ideally Suited for Automatic Insertion
- Complementary NPN Types: BC847CQ
- For Switching and AF Amplifier Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

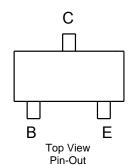
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208<sup>(3)</sup>
- Weight: 0.008 grams (Approximate)







Device Symbol



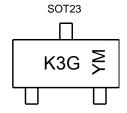
#### Ordering Information (Note 5)

| Part Number | Compliance | Marking | Reel Size (inches) | Quantity per Reel |
|-------------|------------|---------|--------------------|-------------------|
| BC857CQ-7-F | Automotive | K3G     | 7                  | 3,000             |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/product-compliance-definitions/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



K3G = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: E = 2017) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

| Year  | 2017 | 20  | 018 | 2019 | 2   | 020 | 2021 |     | 2022 | 2023 |     | 2024 |
|-------|------|-----|-----|------|-----|-----|------|-----|------|------|-----|------|
| Code  | E    |     | F   | G    |     | Н   |      |     | J    | K    |     | L    |
|       |      |     |     |      |     |     |      |     |      |      |     |      |
| Month | Jan  | Feb | Mar | Apr  | May | Jun | Jul  | Aug | Sep  | Oct  | Nov | Dec  |



### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

| Characteristic               | Symbol           | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage       | V <sub>CBO</sub> | -50   | V    |
| Collector-Emitter Voltage    | V <sub>CEO</sub> | -45   | V    |
| Emitter-Base Voltage         | V <sub>EBO</sub> | -5.0  | V    |
| Continuous Collector Current | I <sub>C</sub>   | -100  | mA   |
| Peak Collector Current       | Ісм              | -200  | mA   |
| Peak Emitter Current         | I <sub>EM</sub>  | -200  | mA   |
| Peak Base Current            | I <sub>BM</sub>  | -200  | mA   |

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                 | Symbol   | Value                            | Unit        |       |  |
|--|----------|----------------------------------|-------------|-------|--|
| Power Dissipation                              | (Note 6) | В                                | 310         | mW    |  |
| Power Dissipation                              | (Note 7) | P <sub>D</sub>                   | 350         | IIIVV |  |
| Thermal Resistance, Junction to Ambient        | (Note 6) | D                                | 403         | °C/W  |  |
| Thermal Resistance, Junction to Ambient        | (Note 7) | R <sub>0JA</sub>                 | 357         | C/VV  |  |
| Thermal Resistance, Junction to Leads (Note 8) |          | R <sub>0</sub> JL                | 350         | °C/W  |  |
| Operating and Storage Temperature Range        |          | T <sub>J,</sub> T <sub>STG</sub> | -65 to +150 | °C    |  |

## ESD Ratings (Note 9)

| Characteristic                             | Symbol  | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V    | 3A          |
| Electrostatic Discharge - Machine Model    | ESD MM  | 400   | V    | С           |

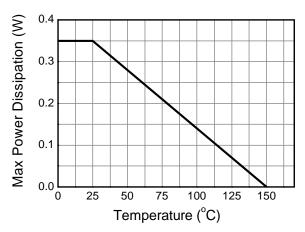
Notes:

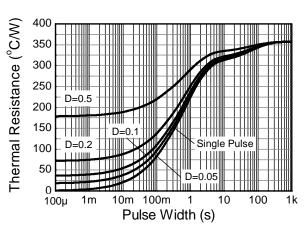
- 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as Note 6, except the device is mounted on 15mm x 15mm 1oz copper.
- 8. Thermal resistance from junction to solder-point (at the end of the leads).

  9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



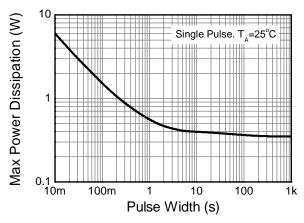
## **Thermal Characteristics and Derating Information**





**Derating Curve** 

**Transient Thermal Impedance** 



**Pulse Power Dissipation** 



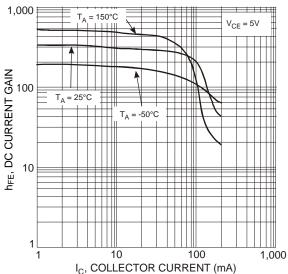
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                 | Symbol                | Min | Тур                | Max   | Unit | Test Condition   |
|--|-----------------------|-----|--------------------|-------|------|--|
| Collector-Base Breakdown Voltage               | BV <sub>CBO</sub>     | -50 | _                  | I     | >    | $I_C = -10\mu A$   |
| Collector-Emitter Breakdown Voltage (Note 10)  | $BV_{CEO}$            | -45 | _                  |       | ٧    | $I_C = -10mA$  |
| Emitter-Base Breakdown Voltage                 | BV <sub>EBO</sub>     | -5  | _                  | 1     | V    | $I_E = -1\mu A$  |
| Collector Cutoff Current                       | 1                     |     |                    | -15   | nA   | V <sub>CB</sub> = -30V   |
| Collector Catoli Carrent                       | I <sub>CBO</sub>      |     |                    | -4    | μΑ   | $V_{CB} = -30V, T_J = +150$ °C   |
| Collector Emitter Cutoff Current               | ICES                  | 1   | _                  | -15   | nA   | V <sub>CE</sub> = -50V   |
| Emitter-Base Cutoff Current                    | I <sub>EBO</sub>      | _   | _                  | -100  | nA   | $V_{EB} = -5V$   |
| Small Signal Current Gain (Note 10)            | h <sub>fe</sub>       | _   | 600                | _     | _    |  |
| Input Impedance (Note 10)                      | h <sub>ie</sub>       | _   | 8.7                | _     | kΩ   | $I_C = -2.0 \text{mA}, V_{CE} = -5 \text{V}$   |
| Output Admittance (Note 10)                    | h <sub>oe</sub>       | _   | 60                 | _     | μS   | f = 1.0kHz   |
| Reverse Voltage Transfer Ratio (Note 10)       | h <sub>re</sub>       | _   | 3x10 <sup>-4</sup> | _     | _    |  |
| DC Current Gain (Note 10)                      | h <sub>FE</sub>       | 420 | 520                | 800   | _    | $I_C = -2.0 \text{mA}, V_{CE} = -5 \text{V}$   |
| Collector Emitter Seturation Voltage (Note 10) | V                     |     | -75                | -300  | mV   | $I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$  |
| Collector-Emitter Saturation Voltage (Note 10) | V <sub>CE</sub> (SAT) |     | -250               | -650  | IIIV | $I_C = -100 \text{mA}, I_B = -5.0 \text{mA}$   |
| Base-Emitter Turn-On Voltage (Note 10)         | .,                    |     | -650               | -750  | mV   | $I_C = -2mA, V_{CE} = -5V$   |
| Base-Emilier Furn-On Voltage (Note 10)         | V <sub>BE(ON)</sub>   | 1   | _                  | -820  | IIIV | $I_C = -10 \text{mA}, V_{CE} = -5 \text{V}$  |
| Base-Emitter Saturation Voltage (Note 10)      | V                     |     | -700               | I     | mV   | $I_C = -10mA$ , $I_B = -0.5mA$   |
| Base-Emilier Saturation voltage (Note 10)      | V <sub>BE(SAT)</sub>  |     | -850               | -1100 | IIIV | $I_C = -100 \text{mA}, I_B = -5 \text{mA}$   |
| Output Capacitance                             | Сово                  |     | 3                  |       | рF   | $V_{CB} = -10V, f = 1.0MHz$  |
| Transition Frequency                           | f⊤                    | 100 | 200                | 1     | MHz  | $V_{CE} = -5V, I_{C} = -10mA,$<br>f = 100MHz   |
| Noise Figure                                   | NF                    | _   | 2                  | 10    | dB   | $V_{CE}$ = -5V, $I_{C}$ = -200 $\mu$ A<br>$R_{S}$ = 2k $\Omega$ , $f$ = 1kHz<br>$\Delta f$ = 200Hz |

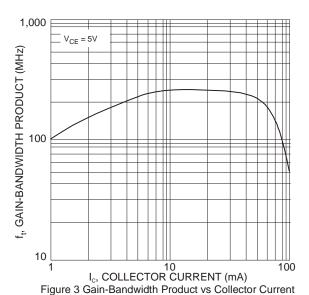
Note: 10. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

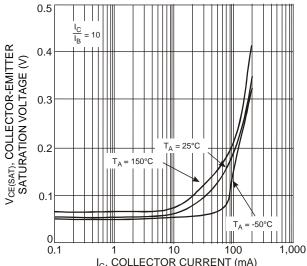


## Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



 $I_{C}, \, \text{COLLECTOR} \, \, \text{CURRENT} \, \, (\text{mA})$  Figure 1 Typical DC Current Gain vs. Collector Current





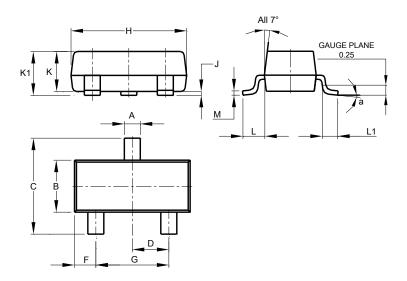
I<sub>C</sub>, COLLECTOR CURRENT (mA)
Figure 2 Typical Collector-Emitter Saturation Voltage
vs. Collector Current



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

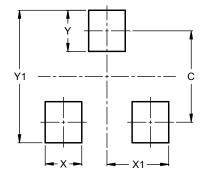


| SOT23 |        |         |       |  |  |
|-------|--------|---------|-------|--|--|
| Dim   | Min    | Max     | Тур   |  |  |
| Α     | 0.37   | 0.51    | 0.40  |  |  |
| В     | 1.20   | 1.40    | 1.30  |  |  |
| С     | 2.30   | 2.50    | 2.40  |  |  |
| D     | 0.89   | 1.03    | 0.915 |  |  |
| F     | 0.45   | 0.60    | 0.535 |  |  |
| G     | 1.78   | 2.05    | 1.83  |  |  |
| Н     | 2.80   | 3.00    | 2.90  |  |  |
| J     | 0.013  | 0.10    | 0.05  |  |  |
| K     | 0.890  | 1.00    | 0.975 |  |  |
| K1    | 0.903  | 1.10    | 1.025 |  |  |
| ١     | 0.45   | 0.61    | 0.55  |  |  |
| L1    | 0.25   | 0.55    | 0.40  |  |  |
| М     | 0.085  | 0.150   | 0.110 |  |  |
| а     | 0°     | 8°      |       |  |  |
| All   | Dimens | ions in | mm    |  |  |

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23



| Dimensions | Value (in mm) |
|------------|---------------|
| С          | 2.0           |
| Х          | 0.8           |
| X1         | 1.35          |
| Υ          | 0.9           |
| Y1         | 2.9           |



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